



THIN FILM TRANSISTOR, SOLID DEVICE, DISPLAY DEVICE
AND MANUFACTURING METHOD OF A THIN FILM TRANSISTOR

ABSTRACT

A thin film transistor which can improve such electric characteristics as off current characteristics, and a manufacturing method of a thin film transistor. A thin film transistor (110) has an n^- source area (112) and an n^- drain area (113) consisting of an n^- silicon film (low concentration area) of about 400Å, which is a silicon film made by performing a crystallization treatment such as an SPC method on an amorphous silicon, and the crystallization treatment is carried out after the ^{implantation}~~injection~~ of impurities to activate the impurities at the same time. A gate electrode (116) is a metal electrode, and is formed after an n^- source area (112) and an n^- drain area (113) are formed. A gate electrode (116), an n^- source area (112) and an n^- drain area (113) are not formed self-alignedly.